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**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #20511**

Generic Copy

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**Issue Date:** 13-Jun-2014

**TITLE:** Change wafer size (5inch to 6inch) at ON Semiconductor fab location in Niigata, Japan. LV47002P-E, LV47004P-E, LV47009P-E and LV47017P-E

**PROPOSED FIRST SHIP DATE:** 16-Sep-2014

**AFFECTED CHANGE CATEGORY(S):** Wafer size change

**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**

Contact your local ON Semiconductor Sales Office or  
<Akio.Nagahama@onsemi.com> <Minoru.Akaishi@onsemi.com>  
<Yukihisa.Kumagai@onsemi.com> <Jyunichi.Kushida@onsemi.com>

**SAMPLES:** Contact your local ON Semiconductor Sales Office or  
<Takashi.Asami@onsemi.com> <Akio.Nagahama@onsemi.com>  
<Jyunichi.Kushida@onsemi.com> <Tetusya.Ishizuka@onsemi.com>

**ADDITIONAL RELIABILITY DATA:** Available  
Contact your local ON Semiconductor Sales Office or  
<Satoru.Fujinuma@onsemi.com>  
<Yukihisa.Kumagai@onsemi.com>

**NOTIFICATION TYPE:**

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

**DESCRIPTION AND PURPOSE:**

This is to increase our supply capacity to support increased demand. Thus to be able to continuously supply products, Wafer size will be changed from 5inch to 6inch for parts identified in this FPCN.



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**RELIABILITY DATA SUMMARY:**

**Reliability Test Results:**

Package name: HZIP25

Test Items	Test Condition	Test Time	Sample Size	Failure
Steady State Operating Life	Tjmax , Vcc(Vdd)opemax	1000h	22	0
Temperature Humidity Bias	Ta=85C,RH=85%, Vcc=Recommended	1000h	22	0
Temperature Humidity Storage	Ta=85C,RH=85%	1000h	22	0
Temperature Cycle	Ta=-55C 30min. ⇔ Ta=150C 30min.	100cyc	22	0
Pressure Cooker	Ta=121C,RH=100% ,205kPa	50h	22	0
High Temperature Storage	Ta=150C	1000h	22	0
Low Temperature Storage	Ta=-55C	1000h	22	0
Resistance to Soldering heat (Flow Soldering)	260C,10s	1time	22	0
Electrostatic Discharge (HBM or MM)	Vcc pin versus each pin, Gnd pin versus each pin (HBM) C=100pF, R=1500ohm, V=+/-1000V (MM) C=200pF, R=0ohm, V=+/-150V	(HMB)3times (MM)1time	3	0

**Notice:**

Temperature Humidity Bias:

Power Dissipation >= 0.1W (Intermittent power application consists of 1-hour ON and 3-hours OFF).

**Judgment Criteria:**

Judgment Criteria are due to the limits of the electrical characteristics in the detail specification.

**ELECTRICAL CHARACTERISTIC SUMMARY:**

There is no change in the electrical performance. Datasheet specifications remain unchanged.

**CHANGED PART IDENTIFICATION:**

Affected products will be identified with date code.

**List of affected General Parts:**

- LV47002P-E
- LV47004P-E
- LV47009P-E
- LV47017P-E